

S3D065V006P SiC Schottky Diode

Features:

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

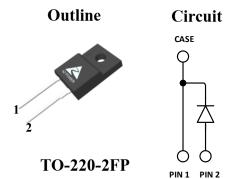
Applications:

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

Benefits:

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit		
V _{RRM}	650	V		
$I_F \ (Te=148^{o}C)$	6	А		
Qc	26	nC		



Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions
VR	DC Peak Reverse Voltage	650	v	$T_J = 25^{\circ}C$
V _{RRM}	Repetitive Peak Reverse	650	V	$T_J = 25^{\circ}C$
V _{RSM}	Surge Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
IF	Continuous Forward Current	17.6 8 6	А	$T_{C} = 25^{\circ}C$ $T_{C} = 135^{\circ}C$ $T_{C} = 148^{\circ}C$
I _{FRM}	Repetitive Peak Forward Surge Current	51 45	А	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 125°C, $T_{\rm P} = 10$ ms, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	66 60	А	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 125°C, $T_{\rm P} = 10$ ms, Half Sine Wave
PD	Power Dissipation	58.8 19.6	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T _{J,max}	Operating Junction Temperature	175	°C	
Tstg	Storage Temperature Range	-55 to 175	°C	

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Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
RthJC	Thermal Resistance		2.55		°C/W

Electrical Characteristics

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Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions	
VDC	DC Blocking Voltage	650			V	$I_R = 100 \mu A, T_J = 25^{\circ}C$	
V _F	Forward Voltage		1.4	1.7	v	$I_F = 6A, T_J = 25^{\circ}C$	
▼ F	rorward vonage		1.7	2.0		$I_F = 6A, T_J = 175^{\circ}C$	
Т	Reverse Current		1	30	μΑ	$V_{R} = 650V, T_{J} = 25^{\circ}C$	
I _R	Reverse Current		10	100		$V_R = 650V, T_J = 175^{\circ}C$	
	Tetal Conseiting Channel		26		nC	0	$I_{\rm F} = 6A, dI/dt = 400A/\mu s$
QC	Total Capacitive Charge		26			$T_J = 25^{\circ}C, V_R = 400V$	
			329			$V_{R} = 1V, T_{J} = 25^{\circ}C, f = 1 \text{ MHz}$	
С	Total Capacitance		45		pF	V_R =200V, T_J =25°C, f=1 MHz	
			43			V_R =400V, T_J =25°C, f=1 MHz	

Typical Performance

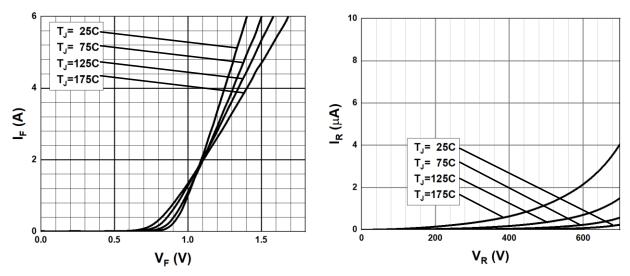


Fig. 1 Forward Characteristics S3D065V006P, Rev. 1.0

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Typical Performance

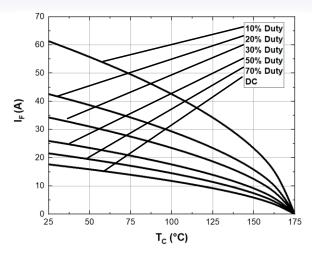


Fig. 3 Current Derating

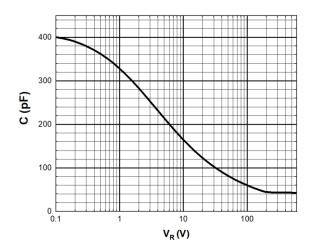


Fig. 5 Capacitance vs. Reverse Voltage

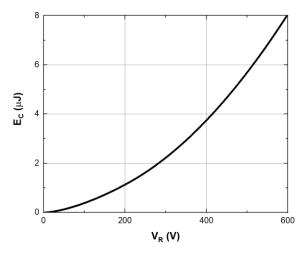


Fig. 7 Capacitance stored Energy S3D065V006P, Rev. 1.0

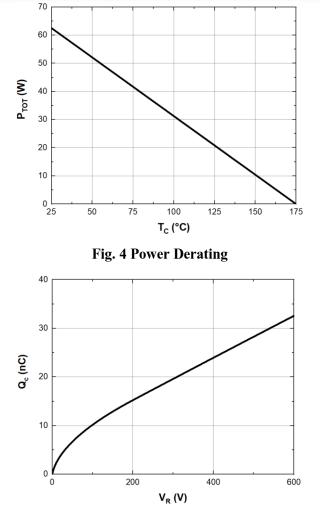


Fig. 6 Recovery Charge vs. Reverse Voltage

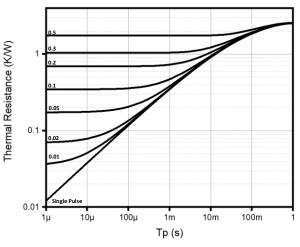


Fig. 8 Thermal Impedance

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MAX

16.1

13.8

10.36

6.8

3.5

1

1.45

0.9

5.4

3.3

1.3

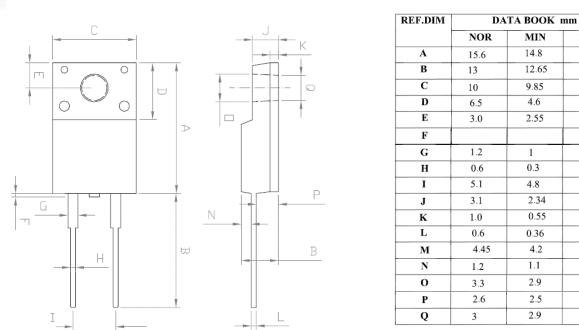
0.8 4.9

1.8

3.5

3.5

3.15



Package TO-220-2FP (Unit: mm)

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